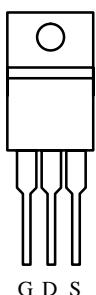


## N-Channel 30-V (D-S), 150°C MOSFET, Logic Level

### Product Summary

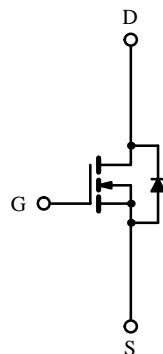
<b>V<sub>(BR)DSS</sub> (V)</b>	<b>r<sub>DS(on)</sub> (Ω)</b>	<b>I<sub>D</sub> (A)</b>
30	0.01	60

TO-220AB



DRAIN connected to TAB

Top View



N-Channel MOSFET

### Absolute Maximum Ratings ( $T_C = 25^\circ\text{C}$ Unless Otherwise Noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V <sub>DS</sub>	30	V
Gate-Source Voltage	V <sub>GS</sub>	$\pm 20$	
Continuous Drain Current	I <sub>D</sub>	60	A
		51	
Pulsed Drain Current	I <sub>DM</sub>	240	A
Avalanche Current	I <sub>AR</sub>	60	
Avalanche Energy	E <sub>AS</sub>	180	mJ
Repetitive Avalanche Energy <sup>a</sup>	E <sub>AR</sub>	90	
Power Dissipation	P <sub>D</sub>	105	W
		42	
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to 150	°C
Lead Temperature (1/16" from case for 10 sec.)	T <sub>L</sub>	300	

### Thermal Resistance Ratings

Parameter	Symbol	Typical	Maximum	Unit
Junction-to-Ambient	R <sub>thJA</sub>	80	1.2	°C/W
Junction-to-Case	R <sub>thJC</sub>			
Case-to-Sink	R <sub>thCS</sub>			

Notes:

a. Duty cycle  $\leq 1\%$

Updates to this data sheet may be obtained via facsimile by calling Siliconix FaxBack, 1-408-970-5600. Please request FaxBack document #70280.  
A SPICE Model data sheet is available for this product (FaxBack document #70525).

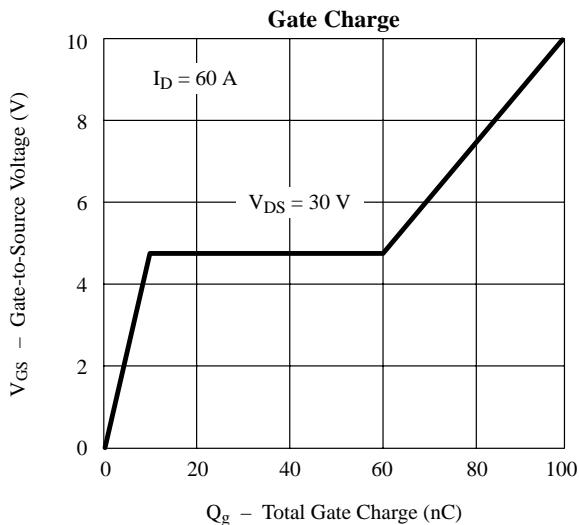
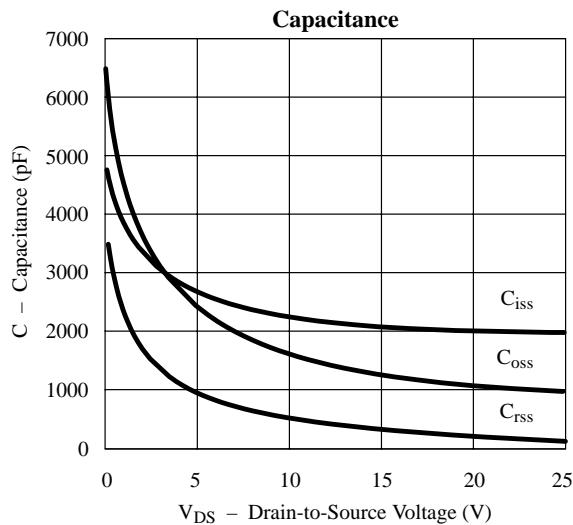
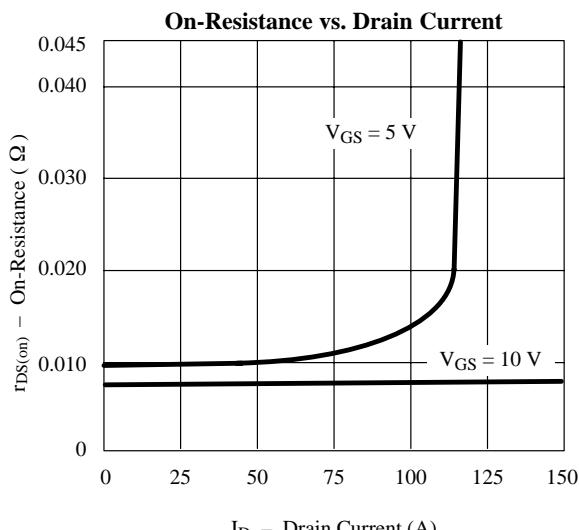
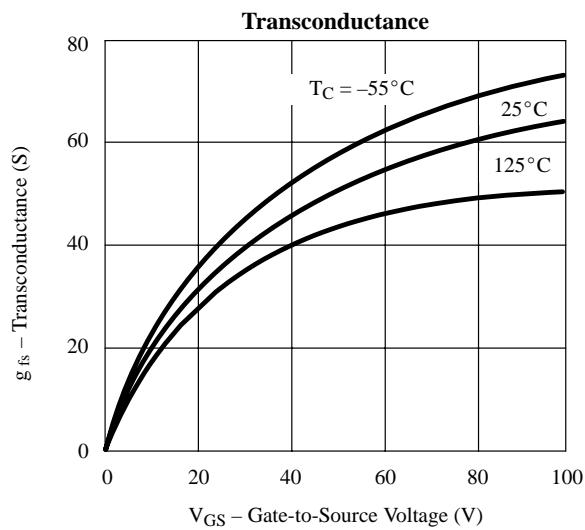
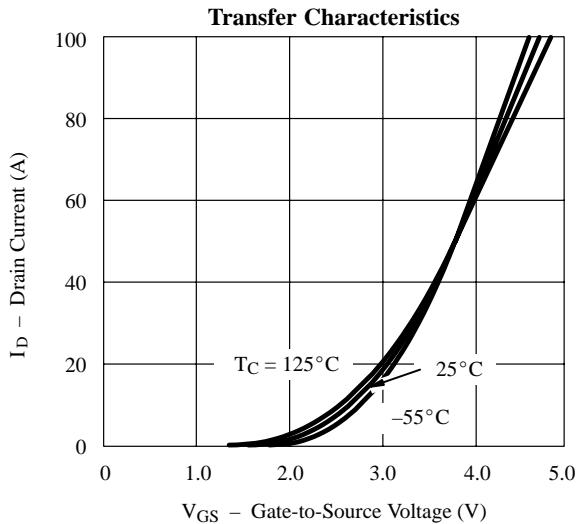
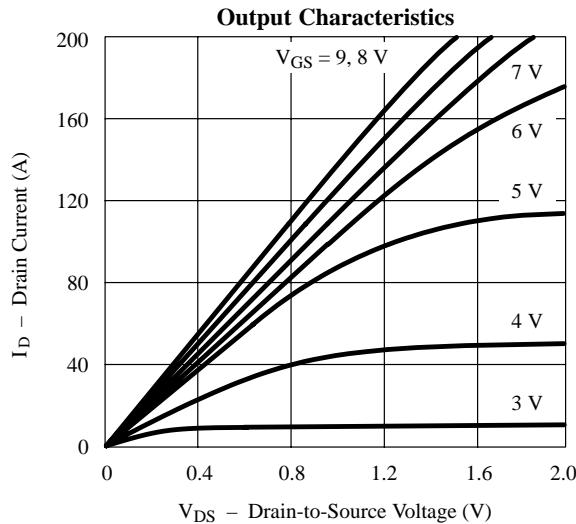
**Specifications ( $T_J = 25^\circ\text{C}$  Unless Otherwise Noted)**

Parameter	Symbol	Test Condition	Min	Typ <sup>a</sup>	Max	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}} = 0 \text{ V}, I_D = 250 \mu\text{A}$	30			V
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}} = V_{\text{GS}}, I_D = 1 \text{ mA}$	0.8		3.0	
Gate-Body Leakage	$I_{\text{GSS}}$	$V_{\text{DS}} = 0 \text{ V}, V_{\text{GS}} = \pm 20 \text{ V}$			$\pm 500$	nA
Zero Gate Voltage Drain Current	$I_{\text{DSS}}$	$V_{\text{DS}} = 24 \text{ V}, V_{\text{GS}} = 0 \text{ V}$			25	
		$V_{\text{DS}} = 24 \text{ V}, V_{\text{GS}} = 0 \text{ V}, T_J = 125^\circ\text{C}$			250	$\mu\text{A}$
On-State Drain Current <sup>b</sup>	$I_{\text{D}(\text{on})}$	$V_{\text{DS}} = 10 \text{ V}, V_{\text{GS}} = 10 \text{ V}$	60			A
Drain-Source On-State Resistance <sup>b</sup>	$r_{\text{DS}(\text{on})}$	$V_{\text{GS}} = 10 \text{ V}, I_D = 30 \text{ A}$		0.007	0.010	
		$V_{\text{GS}} = 5 \text{ V}, I_D = 30 \text{ A}$		0.010	0.015	$\Omega$
		$V_{\text{GS}} = 10 \text{ V}, I_D = 30 \text{ A}, T_J = 125^\circ\text{C}$		0.009	0.014	
Forward Transconductance <sup>b</sup>	$g_{\text{fs}}$	$V_{\text{DS}} = 15 \text{ V}, I_D = 30 \text{ A}$		45		s
<b>Dynamic</b>						
Input Capacitance	$C_{\text{iss}}$	$V_{\text{GS}} = 0 \text{ V}, V_{\text{DS}} = 25 \text{ V}, f = 1 \text{ MHz}$		2600		
Output Capacitance	$C_{\text{oss}}$			1500		pF
Reverse Transfer Capacitance	$C_{\text{rss}}$			750		
Total Gate Charge <sup>c</sup>	$Q_g$	$V_{\text{DS}} = 15 \text{ V}, V_{\text{GS}} = 10 \text{ V}, I_D = 60 \text{ A}$		100	120	
Gate-Source Charge <sup>c</sup>	$Q_{\text{gs}}$			10	15	nC
Gate-Drain Charge <sup>c</sup>	$Q_{\text{gd}}$			45	75	
Turn-On Delay Time <sup>c</sup>	$t_{\text{d}(\text{on})}$	$V_{\text{DD}} = 30 \text{ V}, R_L = 1 \Omega$ $I_D \approx 30 \text{ A}, V_{\text{GEN}} = 10 \text{ V}, R_G = 2.5 \Omega$		14	30	
Rise Time <sup>c</sup>	$t_r$			25	50	ns
Turn-Off Delay Time <sup>c</sup>	$t_{\text{d}(\text{off})}$			65	100	
Fall Time <sup>c</sup>	$t_f$			45	80	
<b>Source-Drain Diode Ratings and Characteristics (<math>T_C = 25^\circ\text{C}</math>)</b>						
Continuous Current	$I_S$				60	
Pulsed Current	$I_{\text{SM}}$				240	A
Forward Voltage <sup>b</sup>	$V_{\text{SD}}$	$I_F = 60 \text{ A}, V_{\text{GS}} = 0 \text{ V}$			1.6	V
Reverse Recovery Time	$t_{\text{rr}}$	$I_F = 60 \text{ A}, dI_F/dt = 100 \text{ A}/\mu\text{s}$		160		ns
Peak Reverse Recovery Current	$I_{\text{RM}(\text{REC})}$			13		A
Reverse Recovery Charge	$Q_{\text{rr}}$			1.0		$\mu\text{C}$

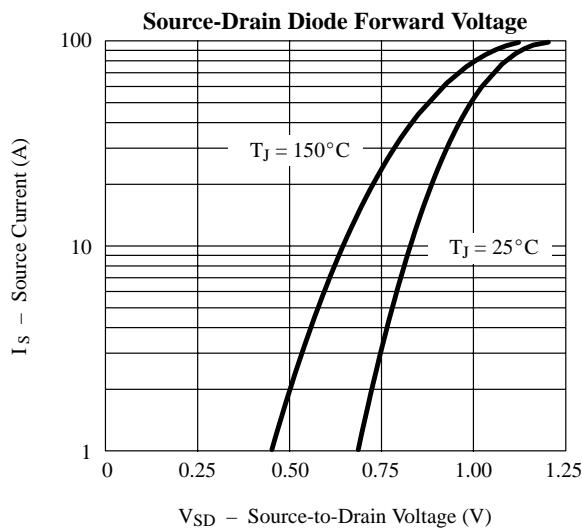
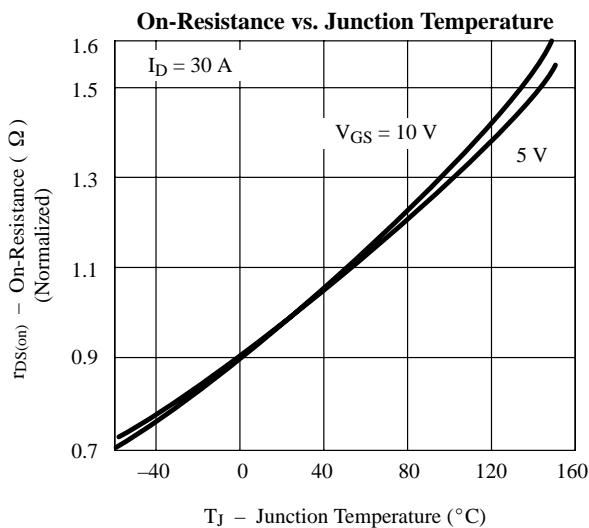
Notes:

- a. For design aid only; not subject to production testing.
- b. Pulse test; pulse width  $\leq 300 \mu\text{s}$ , duty cycle  $\leq 2\%$ .
- c. Independent of operating temperature.

## Typical Characteristics (25°C Unless Otherwise Noted)



## Typical Characteristics (25°C Unless Otherwise Noted)



## Thermal Ratings

